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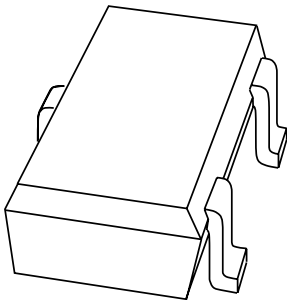
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Kind regards,

Team Nexperia

DATA SHEET



PBSS4140U

40 V low V_{CEsat} NPN transistor

Product data sheet
Supersedes data of 2001 Mar 27

2001 Jul 13

40 V low V_{CEsat} NPN transistor

PBSS4140U

FEATURES

- Low collector-emitter saturation voltage
- High current capabilities.
- Improved device reliability due to reduced heat generation.
- Enhanced performance over SOT231A general purpose packaged transistors.

APPLICATIONS

- General purpose switching and muting
- LCD backlighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT323 plastic package.
PNP complement: PBSS5140U.

MARKING

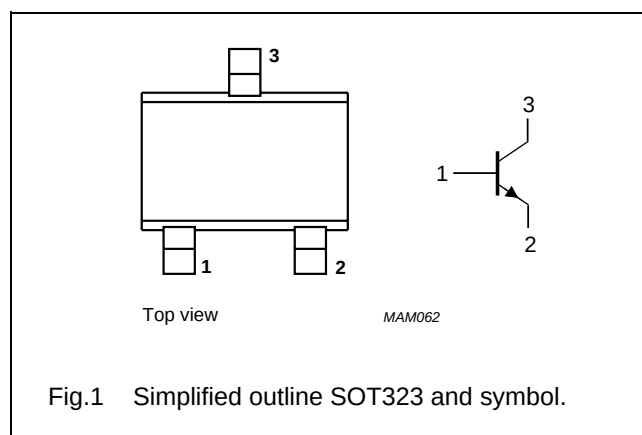
TYPE NUMBER	MARKING CODE
PBSS4140U	41t

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	40	V
I_{CM}	peak collector current	2	A
R_{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	40	V
V_{CEO}	collector-emitter voltage	open base	—	40	V
V_{EBO}	emitter-base voltage	open collector	—	5	V
I_C	collector current (DC)		—	1	A
I_{CM}	peak collector current		—	2	A
I_{BM}	peak base current		—	1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	250	mW
		$T_{amb} \leq 25\text{ °C}$; note 2	—	350	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Notes

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	500	K/W
		in free air; note 2	357	K/W

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

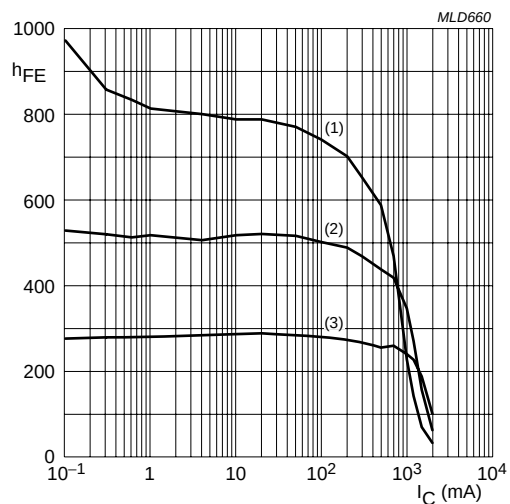
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_C = 0$	—	—	100	nA
		$V_{CB} = 40\text{ V}; I_C = 0; T_{amb} = 150\text{ }^{\circ}\text{C}$	—	—	50	μA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0$	—	—	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	—	—	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	300	—	—	
		$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	300	—	900	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	200	—	—	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	—	—	200	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	—	—	250	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	—	—	500	mV
R_{CEsat}	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	—	260	<500	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	—	—	1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	—	—	1.1	V
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	150	—	—	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0; f = 1\text{ MHz}$	—	—	10	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

40 V low V_{CEsat} NPN transistor

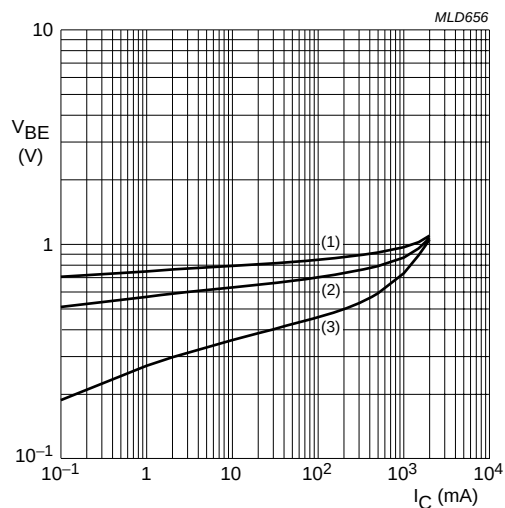
PBSS4140U



$V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -55 \text{ }^{\circ}\text{C}$.

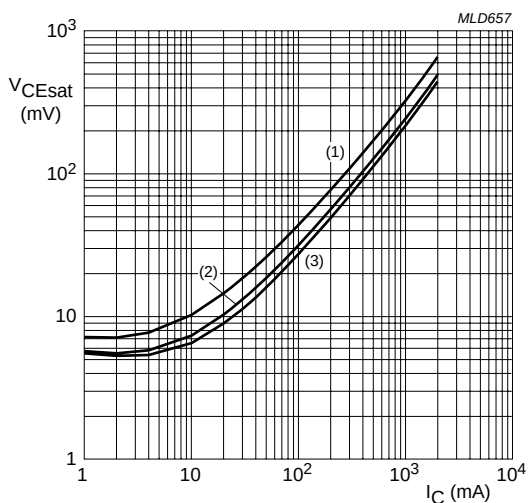
Fig.2 DC current gain as a function of collector current; typical values.



$V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = -55 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.

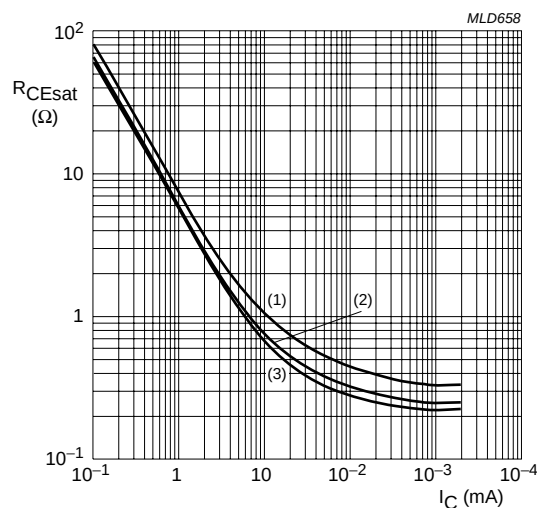
Fig.3 Base-emitter voltage as a function of collector current; typical values.



$I_C/I_B = 10$.

- (1) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -55 \text{ }^{\circ}\text{C}$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



$I_C/I_B = 10$.

- (1) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -55 \text{ }^{\circ}\text{C}$.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

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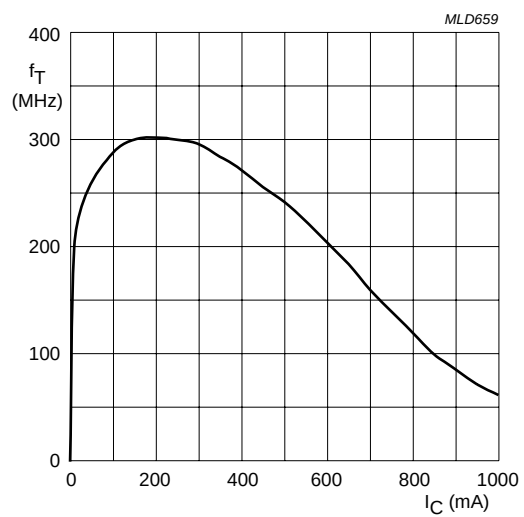
 $V_{CE} = 10$ V.

Fig.6 Transition frequency as a function of collector current; typical values.

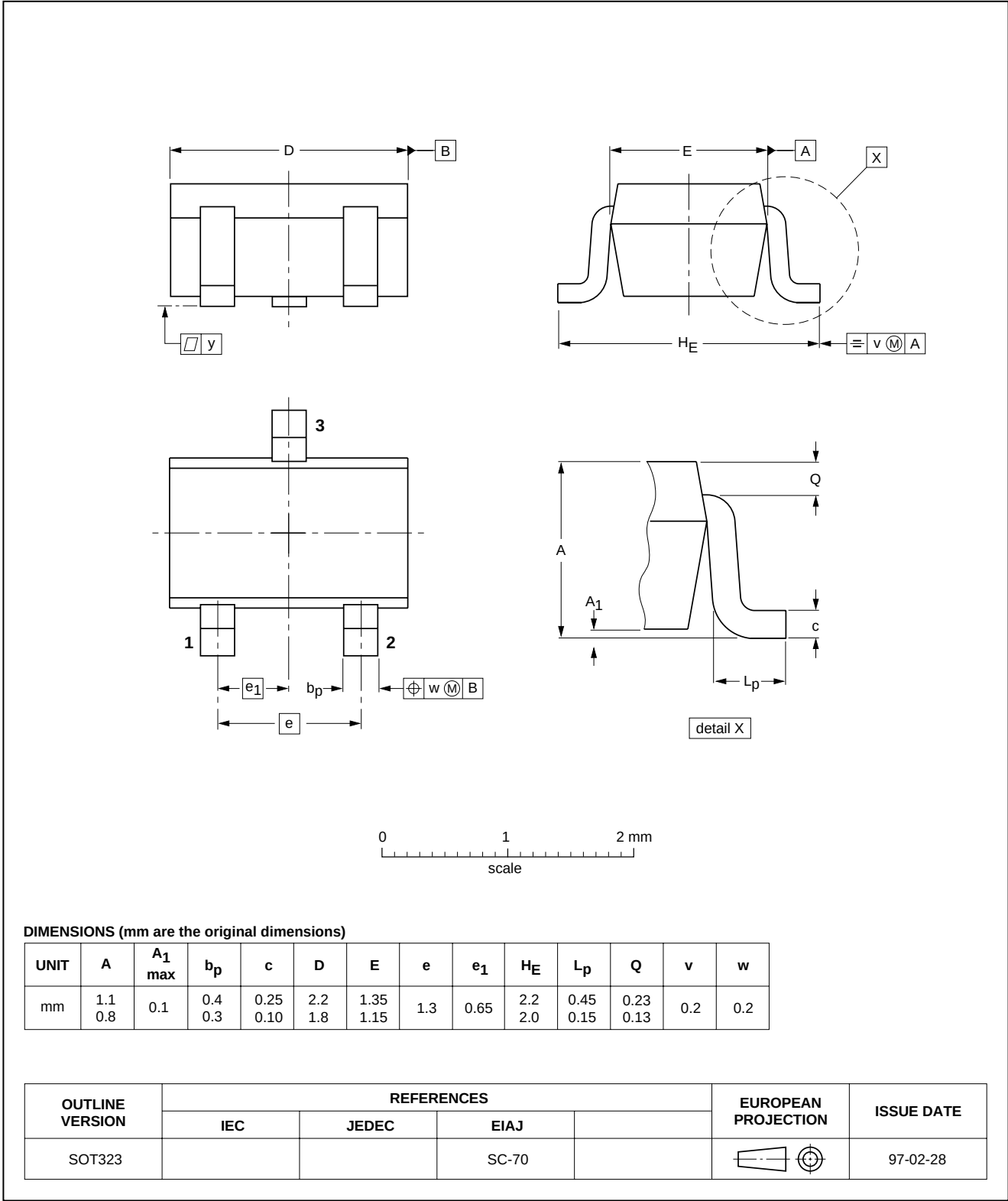
40 V low V_{CEsat} NPN transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



40 V low V_{CEsat} NPN transistor

PBSS4140U

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

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Printed in The Netherlands

613514/02/pp8

Date of release: 2001 Jul 13

Document order number: 9397 750 08427

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